B50T040F

500V N-Channel Power MOSFET

General Description

The B50T040F N-Channel MOSFET uses advanced technology and allows a minimum RDS(ON) and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

Application

- High frequency switching mode power supply
- Electronic ballast
- Motor Driver

Features

- Low Gate Charge
- Low Crss (typical 2.1pF)
- Fast switching
- Improved dv/dt capability
- 100% Avalanche Tested
- Fast Reverse Recovery

Typical Application

V _{DS}	500	V
Rds(on) max	3.6	Ω
ID	4	A

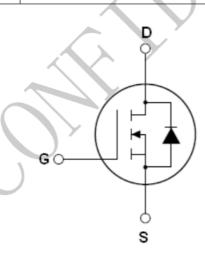


Figure 1. Schematic Diagram

Ordering Information

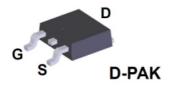
Part Number	Package	Operating Temperature	Packing Type	Marking
B50T040F	TO-252	-40 °C to 105 °C	Tape & Reel 2,500pcs/Reel	B50T040 XXXXXKP XXXXWWF



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Pin Configuration and Marking Information



B50T040 XXXXXKP XXXXWWF

XXXXXK: Lot Code

WW: Week

Figure 2. Pin Configuration and Marking Information

Pin Definition

Pin No.	Name	Description
1	G	Gate
2	D	Drain
3	S	Source

Absolute Maximum Rating (note 1) (Unless otherwise specified, TA=25°C)

Symbol	Parameters	Range	Unit
VDS	Drain-Source Voltage (VGS=0V)	500	V
Vgs	Gate-Source Voltage (VDS=0V)	±30	V
$I_{D(DC)}$	Continuous Drain Current at Tc=25 °C(note 2)	4.0	A
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 to 150	$^{\circ}$
R_{thJC}	Thermal Resistance, Junction-to-Case	2.2	℃/W
R_{thJA}	Thermal Resistance, Junction-to-Ambient	62.5	℃/W

Note 1: Stress beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. Under "recommended operating conditions" the device operation is assured, but some particular parameter may not be achieved. The electrical characteristics table defines the operation range of the device, the electrical characteristics is assured on DC and AC voltage by the test program. For the parameters without minimum and maximum value in the EC table, the typical value defines the operation range, the accuracy is not guaranteed by spec.

Note 2: Limited by maximum junction temperature.



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